Insulated Gate Bipolar Transistors
IGBT-Chips

	Type T_{JM} = 150°C	V_{CES}	$V_{CE(sat)}$ @ I_C		C_{ies} typ.	t_{fi} typ.	Chip type	Chip size dimensions		Source bond wire recommend	Equivalent device data sheet	Dim. out-line
		V	V	A	pF	ns		mm	mils			No.
Low $V_{CE(sat)}$	**IXGD28N30-43**	300	2.1	20	1500	120	IX43	5.64 x 4.67	222 x 184	15 mil x 1	IXGH28N30A	1
	IXGD40N30-5X		1.5	20	2500	220	IX5X	6.58 x 6.58	259 x 259	15 mil x 2	IXGH40N30	26
	IXGD12N60B-3X	600	2.1	12	750	120	IX3X	4.39 x 3.60	173 x 142	12 mil x 1	IXGP12N60B	3
	IXGD31N60-4X		1.8	20	1500	400	IX4X	5.65 x 4.70	222 x 185	15 mil x 1	IXGH31N60	11
	IXGD41N60-5X		1.4	20	2500	450	IX5X	6.59 x 6.59	259 x 259	15 mil x 2	IXGH41N60	26
	IXGD60N60-7Y		1.7	20	3700	360	IX7Y	8.89 x 7.16	350 x 282	15 mil x 3	IXGH60N60B	27
	IXGD200N60B-9X		1.6	20	9000	160	IX9X	14.20 x 10.60	559 x 417	15 mil x 6	IXGN200N60B	23
	IXGD2N100-1M	1000	2.5	2	80	390	IX1M	1.96 x 1.68	77 x 66	5 mil x 1		30
	IXGD4N100-1T		2.7	4	350	390	IX1T	2.54 x 2.54	100 x 100	5 mil x 1		2
	IXGD8N100-2L		2.7	8	600	390	IX2L	3.17 x 3.17	125 x 125	12 mil x 1	IXGP8N100	31
	IXGD12N100-33		3.5	12	750	800	IX33	4.39 x 3.60	173 x 142	12 mil x 1	IXGH12N100	3
	IXGD20N100-4U		2.7	20	1750	280	IX4U	5.77 x 4.96	227 x 195	15 mil x 1	IXGH20N100	12
	IXGD25N100-5T		3.4	20	2750	800	IX5T	6.73 x 6.61	265 x 260	10 mil x 4	IXGH25N100	9
	IXGD25N120-5T	1200	2.9	20	2750	800	IX5T	6.73 x 6.61	265 x 260	10 mil x 4	IXGH25N120	9
	IXGD45N120-7U		2.2	20	4700	390	IX7U	9.51 x 7.21	375 x 284	15 mil x 3	IXGH45N120	32
High Speed	**IXGD28N30A-43**	300	2.1	20	1500	120	IX43	5.64 x 4.67	222 x 184	15 mil x 1	IXGH28N30A	1
	IXGD20N60B-4X	600	2.0	20	1500	150	IX4X	5.65 x 4.70	222 x 185	15mil x 1	IXGH20N60B	11
	IXGD24N60B-4X		2.5	20	1500	120	IX4X	5.65 x 4.70	222 x 185	15mil x 1	IXGH24N60B	11
	IXGD28N60B-4X		1.8	20	1500	200	IX4X	5.65 x 4.70	222 x 185	15mil x 1	IXGH28N60B	11
	IXGD30N60B-5X		1.6	20	2500	190	IX5X	6.58 x 6.58	259 x 259	15 mil x 2	IXGH30N60B	26
	IXGD32N60B-5X		2.3	20	2500	120	IX5X	6.59 x 6.59	259 x 259	15 mil x 2	IXGH32N60B	26
	IXGD40N30A-5X		1.8	20	2500	120	IX5X	6.58 x 6.58	259 x 259	20 mil x 1	IXGH40N30A	26
	IXGD50N60B-7Y		2.2	20	4000	150	IX7Y	8.89 x 7.16	350 x 282	15 mil x 3	IXGH50N60B	27
	IXGD28N90B-5X	900	1.8	20	2500	130	IX5X	6.59 x 6.59	259 x 259	15 mil x 2	IXGH28N90B	26
	IXGD12N100A-33	1000	4.0	12	750	500	IX33	4.39 x 3.60	173 x 142	12 mil x 1	IXGH12N100A	3
	IXGD15N100C-4U		3.5	15	1720	100	IX4U	5.77 x 4.96	227 x 195	15 mil x 1	IXGH15N100C	12
	IXGD25N100A-5T		3.9	20	2750	500	IX5T	6.73 x 6.61	265 x 260	10 mil x 4	IXGH25N100A	9
	IXGD15N120B-4U	1200	3.2	15	1720	160	IX4U	5.77 x 4.96	227 x 195	15 mil x 1	IXGP15N120B	12
	IXGD25N120A-5T		3.9	20	2750	600	IX5T	6.73 x 6.61	265 x 260	10 mil x 4	IXGH25N120A	9
	IXGD35N120B-7U		3.2	20	4200	160	IX7U	9.51 x 7.21	375 x 284	15 mil x 3	IXGH35N120B	32

Notes:

1 Recommended Gate bond wire is 8 mil except 6 mil wire must be used for starred (*) types.
2 Maximum switching limits from packaged device data sheet are given in the respective discrete data sheet.
3 Dice are tested to Vsat limits as indicated up to a maximum of 20A.
4 Recommended die processing thermal budget is not to exceed 365 degrees C for 5 minutes.